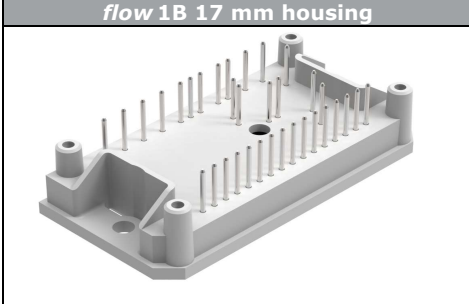
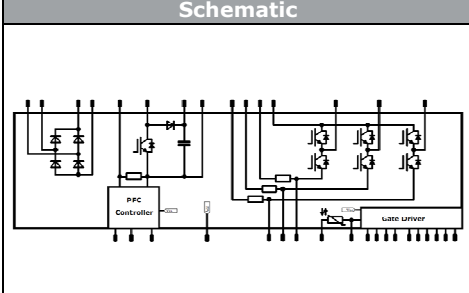




<i>flow</i> IPM 1B	600 V / 10 A
<div style="background-color: #eee; padding: 2px; margin-bottom: 5px;"><b>Features</b></div> <ul style="list-style-type: none"> <li>CIP-topology (converter + inverter + PFC)</li> <li>Optimized for PFC frequencies up to 150 kHz *</li> <li>Integrated PFC controller circuit with programmable DC output voltage and PWM frequency</li> <li>Inverter gate drive including bootstrap circuit for high side power supply</li> <li>Over current and short circuit protection</li> <li>Open emitter or emitter shunts</li> <li>Temperature sensor</li> </ul>	<div style="background-color: #eee; padding: 2px; margin-bottom: 5px;"><b>flow 1B 17 mm housing</b></div> 
<div style="background-color: #eee; padding: 2px; margin-bottom: 5px;"><b>Target Applications</b></div> <ul style="list-style-type: none"> <li>Embedded Drives</li> <li>Industrial Drives</li> </ul>	<div style="background-color: #eee; padding: 2px; margin-bottom: 5px;"><b>Schematic</b></div> 
<div style="background-color: #eee; padding: 2px; margin-bottom: 5px;"><b>Types</b></div> <ul style="list-style-type: none"> <li>20-1B06IPB010RC02-L815A49</li> <li>20-1B06IPB010RC02-L815A49-/3/</li> </ul>	

### Maximum Ratings

$T_j=25^{\circ}\text{C}$ , unless otherwise specified

Parameter	Symbol	Condition	Value	Unit
<b>Input Rectifier Diode</b>				
Repetitive peak reverse voltage	$V_{RRM}$		1600	V
DC forward current	$I_{FAV}$	$T_j = T_{jmax}$ $T_s = 80^{\circ}\text{C}$	13	A
Surge (non-repetitive) forward current	$I_{FSM}$	$t_p = 10\text{ ms}$ 50 Hz half sine wave $T_j = 150^{\circ}\text{C}$	130	A
$I^2t$ -value	$I^2t$		80	$\text{A}^2\text{s}$
Power dissipation	$P_{tot}$	$T_j = T_{jmax}$ $T_s = 80^{\circ}\text{C}$	15	W
Maximum Junction Temperature	$T_{jmax}$		150	$^{\circ}\text{C}$

**Maximum Ratings** $T_j=25^{\circ}\text{C}$ , unless otherwise specified

Parameter	Symbol	Condition	Value	Unit
-----------	--------	-----------	-------	------

**PFC Switch**

Collector-emitter breakdown voltage	$V_{CE}$		650	V
DC collector current	$I_C$	$T_j = T_{jmax}$ $T_s = 80^{\circ}\text{C}$	12	A
Repetitive peak collector current	$I_{CRM}$	$t_p$ limited by $T_{jmax}$	90	A
Turn off safe operating area		$V_{CE} \leq 650\text{ V}$ , $T_j \leq T_{op max}$	90	A
Power dissipation	$P_{tot}$	$T_j = T_{jmax}$ $T_s = 80^{\circ}\text{C}$	19	W
Gate-emitter peak voltage	$V_{GE}$		$\pm 20$	V
Maximum Junction Temperature	$T_{jmax}$		175	$^{\circ}\text{C}$

\* The integrated PFC controller operating at switching frequencies > 100 kHz might show some limitations depending on the application. Please contact our sales representative for further details.

**PFC Inverse Diode**

Peak Repetitive Reverse Voltage	$V_{RRM}$		650	V
DC forward current	$I_F$	$T_j = T_{jmax}$ $T_s = 80^{\circ}\text{C}$	5	A
Repetitive peak forward current	$I_{FRM}$	$t_p$ limited by $T_{jmax}$	12	A
Power dissipation	$P_{tot}$	$T_j = T_{jmax}$ $T_s = 80^{\circ}\text{C}$	10	W
Maximum Junction Temperature	$T_{jmax}$		175	$^{\circ}\text{C}$

**PFC Diode**

Peak Repetitive Reverse Voltage	$V_{RRM}$		650	V
DC forward current	$I_F$	$T_j = T_{jmax}$ $T_s = 80^{\circ}\text{C}$	7	A
Repetitive peak forward current	$I_{FRM}$	$t_p$ limited by $T_{jmax}$	35	A
Power dissipation	$P_{tot}$	$T_j = T_{jmax}$ $T_s = 80^{\circ}\text{C}$	11	W
Maximum Junction Temperature	$T_{jmax}$		175	$^{\circ}\text{C}$

**Maximum Ratings** $T_j=25^{\circ}\text{C}$ , unless otherwise specified

Parameter	Symbol	Condition	Value	Unit
-----------	--------	-----------	-------	------

**Inverter Switch**

Collector-emitter breakdown voltage	$V_{CE}$		600	V
DC collector current	$I_C$	$T_j = T_{jmax}$ $T_s = 80^{\circ}\text{C}$	8	A
Repetitive peak collector current	$I_{CRM}$	$t_p$ limited by $T_{jmax}$	30	A
Turn off safe operating area		$V_{CE} \leq 600\text{ V}$ , $T_j \leq 150^{\circ}\text{C}$	20	A
Power dissipation	$P_{tot}$	$T_j = T_{jmax}$ $T_s = 80^{\circ}\text{C}$	16	W
Gate-emitter peak voltage	$V_{GE}$		$\pm 20$	V
Short circuit ratings	$t_{SC}$ $V_{CC}$	$T_j \leq 150^{\circ}\text{C}$ $V_{GE} = 15\text{ V}$	5 400	$\mu\text{s}$ V
Maximum Junction Temperature	$T_{jmax}$		175	$^{\circ}\text{C}$

**Inverter Diode**

Peak Repetitive Reverse Voltage	$V_{RRM}$		600	V
DC forward current	$I_F$	$T_j = T_{jmax}$ $T_s = 80^{\circ}\text{C}$	8	A
Power dissipation	$P_{tot}$	$T_j = T_{jmax}$ $T_s = 80^{\circ}\text{C}$	14	W
Maximum Junction Temperature	$T_{jmax}$		175	$^{\circ}\text{C}$

**PFC Shunt**

DC forward current	$I_F$	$T_c = 25^{\circ}\text{C}$	10	A
Power dissipation	$P_{tot}$	$T_c = 25^{\circ}\text{C}$	4	W

**PFC Controller\***

VCC supply voltage	$V_{CC}$	$V_{CC}$ common with gate driver IC	26	V
Vsense voltage	$V_{VSENSE}$		26	V
Vsense current	$I_{VSENSE}$		800	$\mu\text{A}$
FREQ pin voltage	$V_{FREQ}$		5,3	V
Maximum Junction Temperature	$T_{jmax}$		125	$^{\circ}\text{C}$

\*For more information please contact VIN sales representative for the updated release of ICE3PCS02 datasheet

**DC - Shunt**

DC forward current	$I_F$		8	A
Power dissipation	$P_{tot}$		2	W

**Maximum Ratings** $T_j=25^{\circ}\text{C}$ , unless otherwise specified

Parameter	Symbol	Condition	Value	Unit
-----------	--------	-----------	-------	------

**DC link Capacitor**

Maximum DC voltage	$V_{MAX}$	$T_c = 25^{\circ}\text{C}$	500	V
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**Gate Driver\***

Supply voltage	$U_{CC}$		20	V
Input voltage (LIN, HIN, EN)	$U_{IN}$		10	V
Output voltage (FAULT)	$U_{OUT}$		VCC+0,5	V

\* for more information see infineon's datasheet 6ED003L02-F2

**Thermal Properties**

Storage temperature	$T_{stg}$		-40...+125	$^{\circ}\text{C}$
Operation temperature under switching con	$T_{op}$		-40...+(Tjmax - 25)	$^{\circ}\text{C}$

**Isolation Properties**

Isolation voltage	$V_{is}$	$t = 2\text{ s}$ DC voltage	4000	V
Creepage distance			min 12,7	mm
Clearance			min 12,7	mm
Comparative tracking index	CTI		>200	



Characteristic Values

Parameter	Symbol	Conditions					Value			Unit
		$V_{GE}$ [V]	$V_{GS}$ [V]	$V_F$ [V] $V_{CE}$ [V] $V_{DS}$ [V]	$I_C$ [A] $I_F$ [A] $I_D$ [A]	$T_j$ [°C]	Min	Typ	Max	
<b>Input Rectifier Diode</b>										
Forward voltage	$V_F$				7	25 125		1,04 0,97		V
Threshold voltage (for power loss calc. only)	$V_{to}$				7	25 125		0,87 0,74		V
Slope resistance (for power loss calc. only)	$r_t$				7	25 125		25 33		mΩ
Reverse current	$I_r$			1600		25			0,01	mA
Thermal resistance junction to sink	$R_{th(j-s)}$	phase-change material $\lambda = 3,4$ W/mK						4,56		K/W

<b>PFC Switch</b>												
Gate emitter threshold voltage	$V_{GE(th)}$	$V_{CE} = V_{GE}$				0,0003	25	3,3	4	4,7	V	
Collector-emitter saturation voltage	$V_{CEsat}$		15			10	25 125		1,28 1,28	1,9	V	
Collector-emitter cut-off	$I_{CES}$		0	650			25			0,04	mA	
Turn-on delay time	$t_{d(on)}$	$U_{cc} = 15$ V	400	10	25 125	25	25 125	21 20	6 8	160 192	ns	
Rise time	$t_r$											
Turn-off delay time	$t_{d(off)}$											
Fall time	$t_f$											
Turn-on energy loss	$E_{on}$											0,086 0,084
Turn-off energy loss	$E_{off}$											0,034 0,061
Input capacitance	$C_{ies}$							2100				
Output capacitance	$C_{oss}$	$f = 1$ MHz	0	25		25		45			pF	
Reverse transfer capacitance	$C_{rss}$							7,7				
Thermal resistance junction to sink	$R_{th(j-s)}$	phase-change material $\lambda = 3,4$ W/mK						4,96			K/W	

<b>PFC Inverse Diode</b>											
Diode forward voltage	$V_F$				6	25 125		1,23	1,73 0,97	2,15	V
Thermal resistance junction to sink	$R_{th(j-s)}$	phase-change material $\lambda = 3,4$ W/mK						9,56			K/W

<b>PFC Diode</b>												
Forward voltage	$V_F$				8	25 125		1,65 1,55	2,1		V	
Reverse leakage current	$I_{rm}$		400	10		25				160	μA	
Peak recovery current	$I_{RRM}$	$U_{cc} = 15$ V	400	10	25 125	25	25 125	3 3	16,7 16	0,03 0,04	A	
Reverse recovery time	$t_{rr}$											
Reverse recovery charge	$Q_{rr}$											0,0060 0,009
Reverse recovered energy	$E_{rec}$											711 893
Peak rate of fall of recovery current	$(di_{rr}/dt)_{max}$											
Thermal resistance junction to sink	$R_{th(j-s)}$											phase-change material $\lambda = 3,4$ W/mK

<b>PFC Shunt</b>											
$R_4$ value	$R$							40			mΩ

**Characteristic Values**

Parameter	Symbol	Conditions					Value			Unit
		$V_{GE}$ [V] $V_{GS}$ [V]	$V_r$ [V] $V_{CE}$ [V] $V_{DS}$ [V]	$I_c$ [A] $I_F$ [A] $I_D$ [A]	$T_j$ [°C]	Min	Typ	Max		
<b>Inverter Switch</b>										
Gate emitter threshold voltage	$V_{GE(th)}$	$V_{CE} = V_{GE}$			0,00017	25	4,4	5	5,6	V
Collector-emitter saturation voltage*	$V_{CEsat}$		15		10	25 125	1,7	2,20 2,32	2,95	v
Collector-emitter cut-off current incl. Diode	$I_{CES}$		0	600		25			0,1	mA
Gate-emitter leakage current	$I_{GES}$		20	0		25			120	nA
Integrated Gate resistor	$R_{gint}$							none		$\Omega$
Turn-on delay time **	$t_{d(on)}$					25 125		582 631		ns
Rise time	$t_r$					25 125		20 25		
Turn-off delay time **	$t_{d(off)}$					25 125		837 950		
Fall time	$t_f$					25 125		16 22		
Turn-on energy loss	$E_{on}$					25 125		0,1950 0,3241		mWs
Turn-off energy loss	$E_{off}$					25 125		0,1611 0,2042		
Input capacitance	$C_{ies}$							655		pF
Output capacitance	$C_{oss}$	$f = 1$ MHz	0	25		25		37		
Reverse transfer capacitance	$C_{rss}$							22		
Gate charge	$Q_G$		15	480	10	25		64		nC
Thermal resistance junction to sink	$R_{th(j-s)}$	phase-change material $\lambda = 3,4$ W/mK						5,79		K/W
* chip data ** including gate driver										
<b>Inverter Diode</b>										
Diode forward voltage	$V_F$				10	25 125	1,5	2,23 2,18	2,85	v
Peak reverse recovery current	$I_{RRM}$					25 125		6 6		A
Reverse recovery time	$t_{rr}$					25 125		179 276		ns
Reverse recovered charge	$Q_{rr}$					25 125		0,3566 0,6738		$\mu$ C
Peak rate of fall of recovery current	$(di_{rr}/dt)_{max}$					25 125		181 46		A/ $\mu$ s
Reverse recovered energy	$E_{rec}$					25 125		0,0867 0,1610		mWs
Thermal resistance junction to sink	$R_{th(j-s)}$	phase-change material $\lambda = 3,4$ W/mK						6,66		K/W
<b>DC - Shunt</b>										
$R_2$ value	$R$					25		30		m $\Omega$
<b>DC link Capacitor</b>										
C value	C							100		nF

**Characteristic Values**

Parameter	Symbol	Conditions					Value			Unit					
		$V_{GE}$ [V]	$V_{GS}$ [V]	$V_f$ [V]	$V_{CE}$ [V]	$V_{DS}$ [V]	$I_c$ [A]	$I_f$ [A]	$I_D$ [A]		$T_j$ [°C]	Min	Typ	Max	
<b>Gate Driver</b>															
Supply voltage	$U_{CC}$									13	15	17,5	V		
Quiescent Vcc supply current	$I_{QCC}$	$U_{LIN} = 0\text{ V}; U_{HIN} = 3,3\text{ V}$										1,3	2	mA	
Input voltage (LIN, HIN, EN)	$U_{IN}$									0		5	V		
Logic "0" input voltage (LIN, HIN)	$U_{IH}$									1,7	2,1	2,4			
Logic "1" input voltage (LIN, HIN)	$U_{IL}$	$U_{CC} = 15\text{ V}$									0,7	0,9		1,1	
Positive going threshold voltage (EN)	$U_{EN,TH+}$									1,9	2,1	2,3			
Negative going threshold voltage (EN)	$U_{EN,TH-}$									1,1	1,3	1,5			
Input clamp voltage (LIN, HIN, EN)	$U_{IN,CLAMP}$	$I_{IN} = 4\text{ mA}$									9	10,3		12	
ITRIP positive going threshold	$U_{TR,TH+}$									380	445	510	mV		
Input bias current LIN high	$I_{LIN+}$	$U_{LIN} = 3,3\text{ V}$					25					70	100	$\mu\text{A}$	
Input bias current LIN low	$I_{LIN-}$	$U_{LIN} = 0\text{ V}$										110	200		
Input bias current HIN high	$I_{HIN+}$	$U_{HIN} = 3,3\text{ V}$										70	100		
Input bias current HIN low	$I_{HIN-}$	$U_{HIN} = 0\text{ V}$										110	120		
Input bias current EN high	$I_{EN+}$	$U_{HIN} = 3,3\text{ V}$										45	120		
Output voltage (FAULT)	$U_{FLT}$										0		$U_{CC}$		V
Low on resistor of pull down trans. (FAULT)	$R_{ON,FLT}$	$U_{FAULT} = 0,5\text{ V}$										45,0	100	$\Omega$	
Pulse width for ON or OFF	$t_{IN}$									1			$\mu\text{s}$		
Turn-on propagation delay (LIN, HIN)	$t_{ON}$									400	530	800	ns		
Turn-off propagation delay (LIN, HIN)	$t_{OFF}$	$U_{LIN/HIN} = 0\text{ V or } 3,3\text{ V}$									360	490		760	
FAULT reset time	$t_{RST}$										4		ms		
Fixed deadtime between high and low side	$t_{DT}$	$U_{LIN/HIN} = 0\text{ V \& } 3,3\text{ V}$									150	310		ns	
<b>PFC Controller</b>															
Supply voltage*	$V_{CC}$									15		26	V		
VCC turn-on threshold	$V_{CCon}$									11,5	12,0	12,9	V		
VCC turn-off threshold	$V_{CCUVLO}$									10,5	11,0	11,9	V		
Operating current with active GATE	$I_{CCHG}$	$C_L = 1\text{ nF}$										6,4	8,5	mA	
Operating current during standby	$I_{CCstby}$										3,5	4,7	mA		
PFC switching frequency	$F_{SWnom}$	Set with an internal resistor $R_{FREQ} = 91\text{ k}\Omega$ **										50		kHz	
PFC disable threshold	$V_{disPFC}$	pull Vsense higher than Vdis PFC to disable PFC operation									14			V	
DC link voltage	DC2+	Set with an internal resistor divider***					25				325		410	V	
DC link threshold (OVP1) low to high	$V_{OVP1L2H}$											108		%	
DC link threshold (OVP1) high to low	$V_{OVP1H2L}$	relative to output voltage with VSENSE pin unconnected											100		%
Blanking time for OVP1	$t_{OVP1}$	VSENSE pin voltage $V_{DCLink}/130$											12		$\mu\text{s}$
DC link threshold (OVP1) hysteresis	$V_{OVP1,HYS}$										6	8	11	%	
DC link threshold (OVP2) low to high	$V_{OVP2L2H}$										428	443	460	V	
DC link threshold (OVP2) high to low	$V_{OVP2H2L}$	relative to OVP2										92		%	
Blanking time for OVP2	$t_{OVP2}$										12		$\mu\text{s}$		
*recommended supply voltage range: 15-18 V **switching frequency is settable by an external resistor between pins 14-16 (see figure on page24 for values) ***DC link voltage is settable by an external resistor between pins 14-15 (see figure on page24 for values)															
<b>Thermistor</b>															
Rated resistance	$R$						25				22000		$\Omega$		
Deviation of $R_{100}$	$\Delta R/R$	$R_{100} = 1486\ \Omega$						100	-12			12	%		
Power dissipation	$P$						25				200		mW		
Power dissipation constant							25				2		mW/K		
B-value	$B_{(25/50)}$	Tol. $\pm 3\%$						25				3950	K		
B-value	$B_{(25/100)}$	Tol. $\pm 3\%$						25				3998	K		
Vincotech NTC Reference												B			

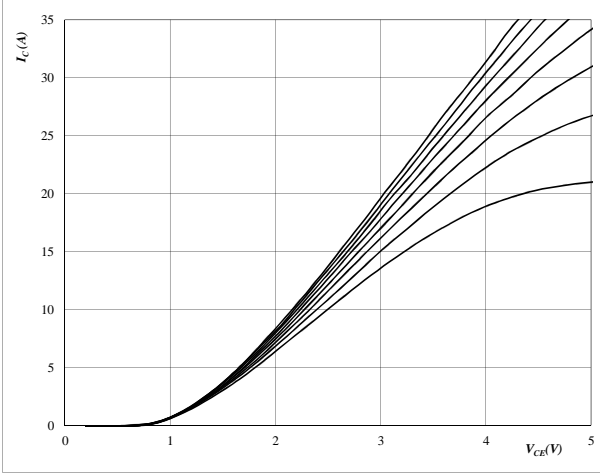


### Output Inverter

**figure 1. Output inverter IGBT**

**Typical output characteristics**

$I_C = f(V_{CE})$



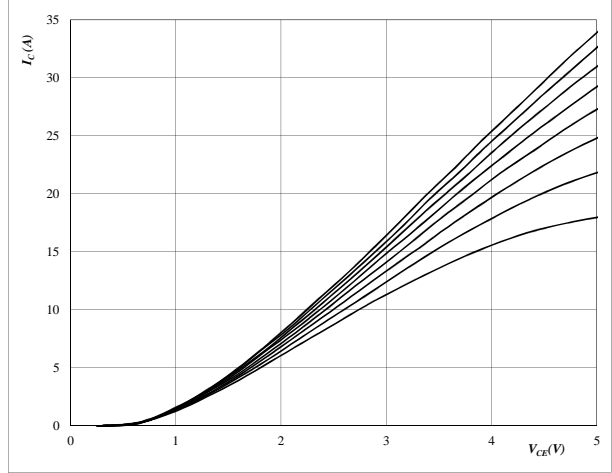
**At**

- $t_p = 250 \mu s$
- $T_j = 25 \text{ }^\circ C$
- $U_{CC}$  from 10 V to 17 V in steps of 1 V

**figure 2. Output inverter IGBT**

**Typical output characteristics**

$I_C = f(V_{CE})$



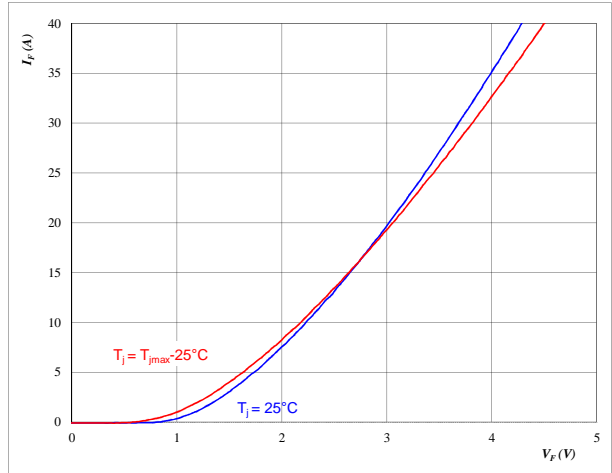
**At**

- $t_p = 250 \mu s$
- $T_j = 125 \text{ }^\circ C$
- $U_{CC}$  from 10 V to 17 V in steps of 1 V

**figure 3. Output inverter FWD**

**Typical diode forward current as a function of forward voltage**

$I_F = f(V_F)$



**At**

- $t_p = 250 \mu s$



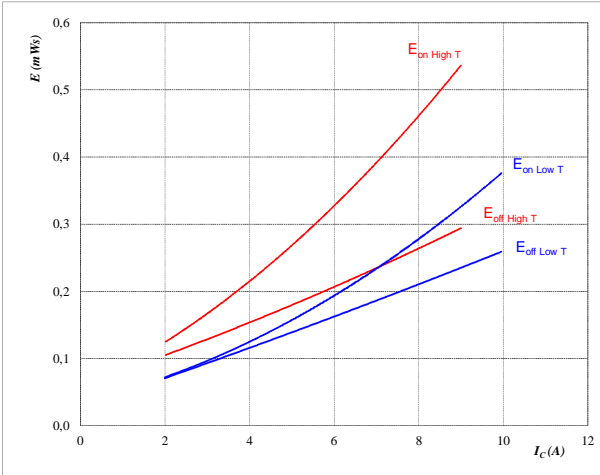


### Output Inverter

**figure 4. Output inverter IGBT**

**Typical switching energy losses as a function of collector current**

$E = f(I_C)$



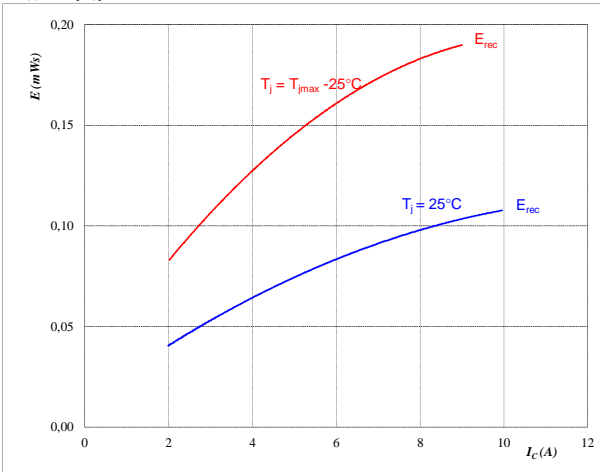
With an inductive load at

- $T_j = 25/125\text{ }^\circ\text{C}$
- $V_{CE} = 400\text{ V}$
- $U_{CC} = 15\text{ V}$

**figure 5. Output inverter FWD**

**Typical reverse recovery energy loss as a function of collector current**

$E_{rec} = f(I_C)$



With an inductive load at

- $T_j = 25/125\text{ }^\circ\text{C}$
- $V_{CE} = 400\text{ V}$
- $U_{CC} = 15\text{ V}$

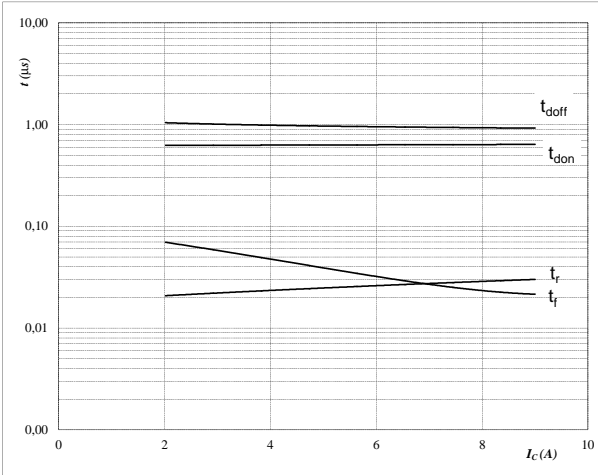


### Output Inverter

**figure 6. Output inverter IGBT**

**Typical switching times as a function of collector current**

$t = f(I_C)$



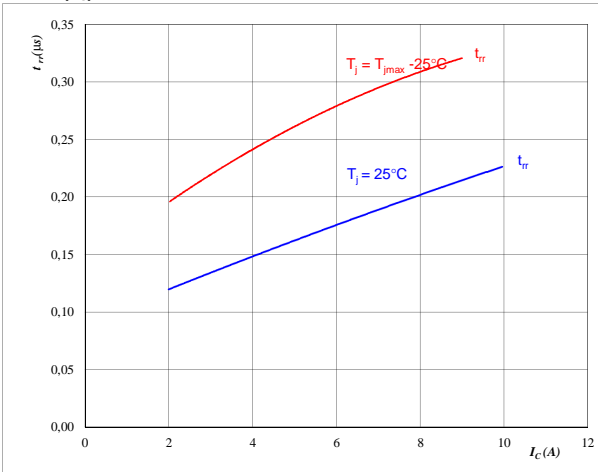
With an inductive load at

- $T_j = 125 \text{ } ^\circ\text{C}$
- $V_{CE} = 400 \text{ V}$
- $U_{CC} = 15 \text{ V}$

**figure 7. Output inverter FWD**

**Typical reverse recovery time as a function of collector current**

$t_{rr} = f(I_C)$



**At**

- $T_j = 25/125 \text{ } ^\circ\text{C}$
- $V_{CE} = 400 \text{ V}$
- $U_{CC} = 15 \text{ V}$

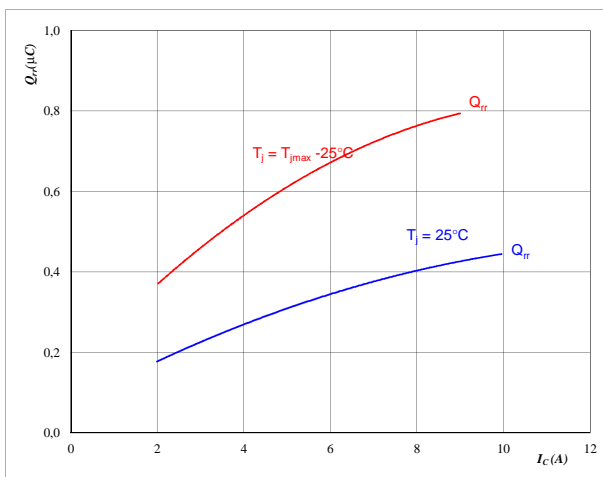


### Output Inverter

**figure 8. Output inverter FWD**

**Typical reverse recovery charge as a function of collector current**

$$Q_{rr} = f(I_c)$$



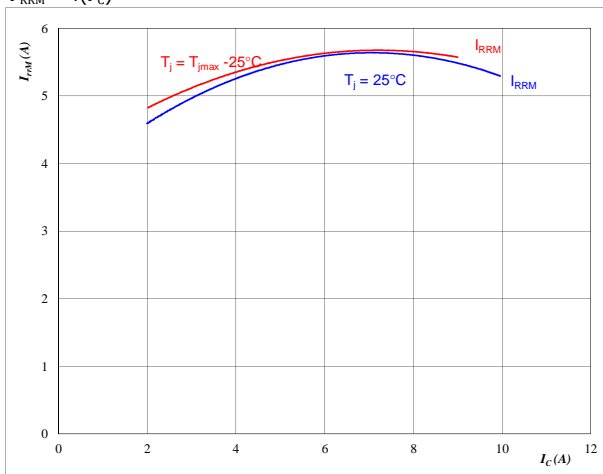
**At**

$T_j = 25/125 \text{ } ^\circ\text{C}$   
 $V_{CE} = 400 \text{ V}$   
 $U_{CC} = 15 \text{ V}$

**figure 9. Output inverter FWD**

**Typical reverse recovery current as a function of collector current**

$$I_{RRM} = f(I_c)$$



**At**

$T_j = 25/125 \text{ } ^\circ\text{C}$   
 $V_{CE} = 400 \text{ V}$   
 $U_{CC} = 15 \text{ V}$

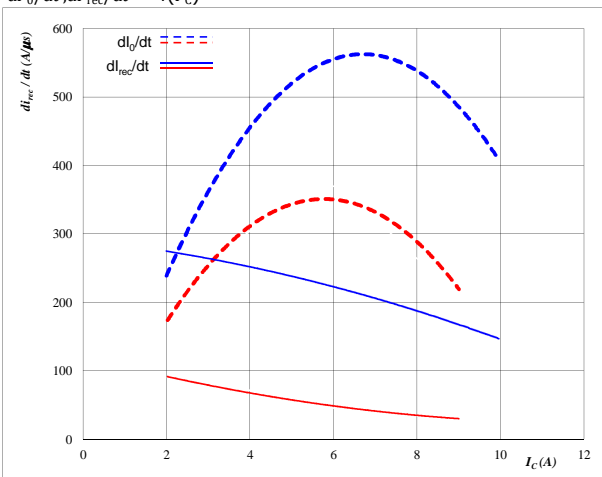


### Output Inverter

**figure 10. Output inverter FWD**

**Typical rate of fall of forward and reverse recovery current as a function of collector current**

$$dI_0/dt, dI_{rec}/dt = f(I_C)$$



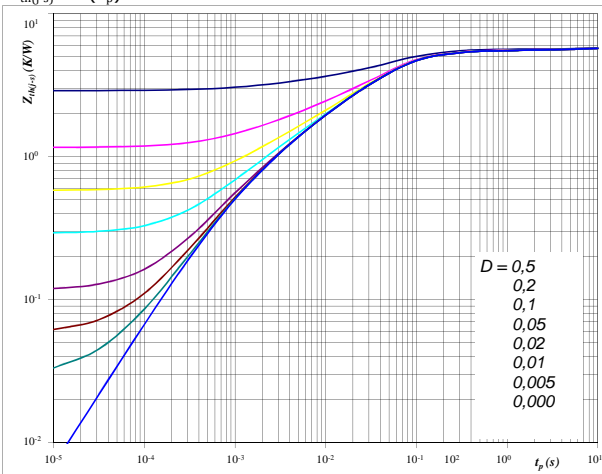
**At**

$T_j = 25/125 \text{ } ^\circ\text{C}$   
 $V_{CE} = 400 \text{ V}$   
 $U_{CC} = 15 \text{ V}$

**figure 11. Output inverter IGBT**

**IGBT transient thermal impedance as a function of pulse width**

$$Z_{th(j-s)} = f(t_p)$$



**At**

$D = t_p / T$   
 $R_{th(j-s)} = 5,79 \text{ K/W}$

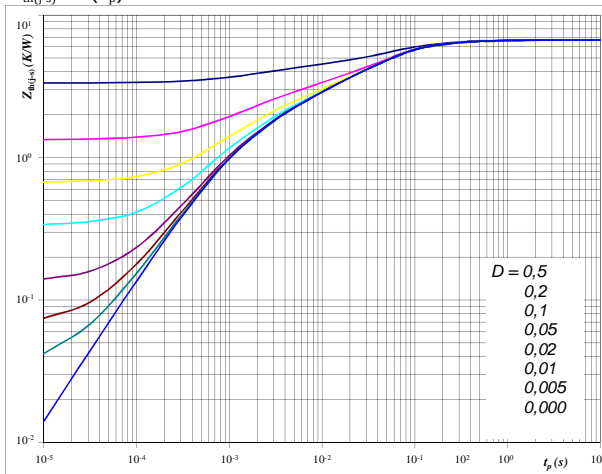
IGBT thermal model values

R (K/W)	Tau (s)
3,03E-01	6,63E+00
6,11E-01	2,13E-01
3,21E+00	4,88E-02
8,43E-01	1,03E-02
5,62E-01	2,85E-03
2,59E-01	7,40E-04

**figure 12. Output inverter FWD**

**FWD transient thermal impedance as a function of pulse width**

$$Z_{th(j-s)} = f(t_p)$$



**At**

$D = t_p / T$   
 $R_{th(j-s)} = 6,66 \text{ K/W}$

FWD thermal model values

R (K/W)	Tau (s)
6,16E-01	3,13E-01
3,07E+00	5,41E-02
7,56E-01	2,30E-02
1,19E+00	4,70E-03
9,47E-01	9,78E-04
7,59E-02	7,51E-04

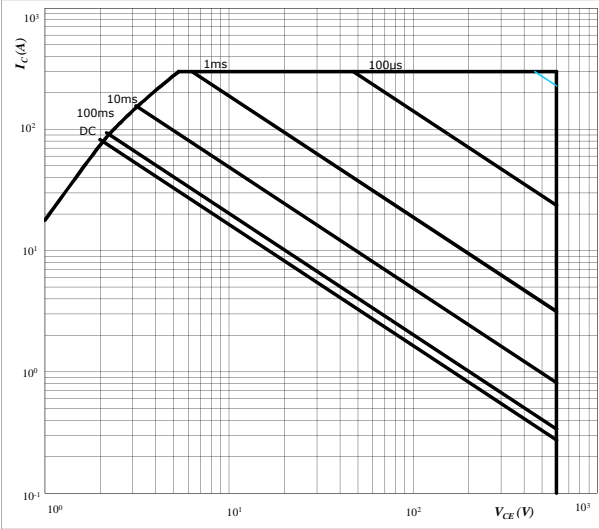


### Output Inverter

**figure 17. Output inverter IGBT**

**Safe operating area as a function of collector-emitter voltage**

$I_C = f(V_{CE})$



**At**

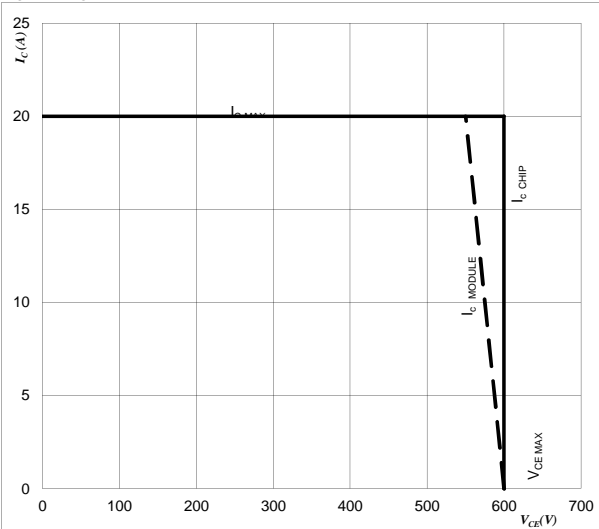
$$T_j \leq T_{jmax}$$

$$U_{CC} = 15 \text{ V}$$

**figure 18. Output inverter IGBT**

**Reverse bias safe operating area**

$I_C = f(V_{CE})$



**At**

$$T_j = T_{jmax} - 25 \text{ } ^\circ\text{C}$$

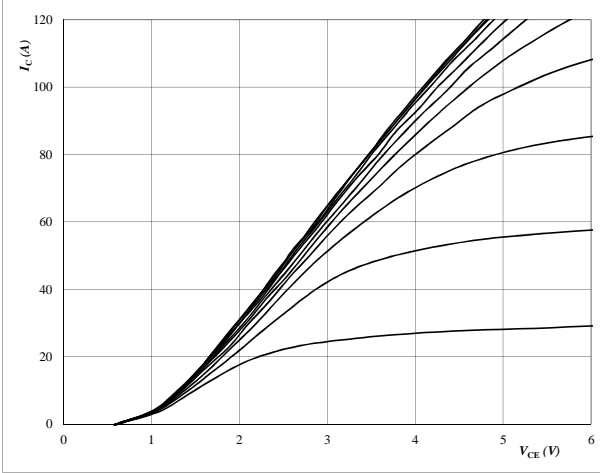


PFC

figure 1. PFC IGBT

Typical output characteristics

$I_C = f(V_{CE})$



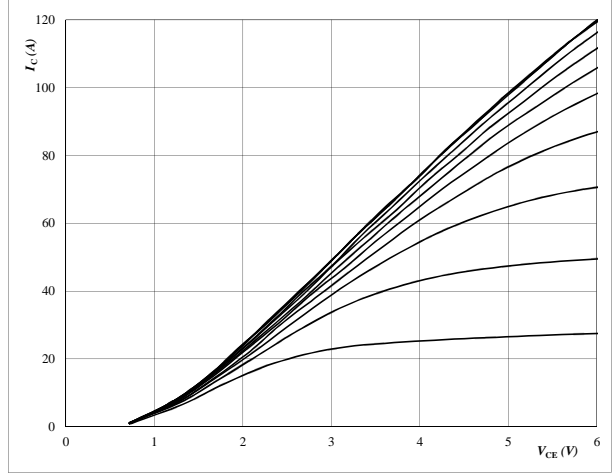
At

$t_p = 250 \mu s$   
 $T_j = 25 \text{ }^\circ C$   
 $U_{CC}$  from 7 V to 17 V in steps of 1 V

figure 2. PFC IGBT

Typical output characteristics

$I_C = f(V_{CE})$



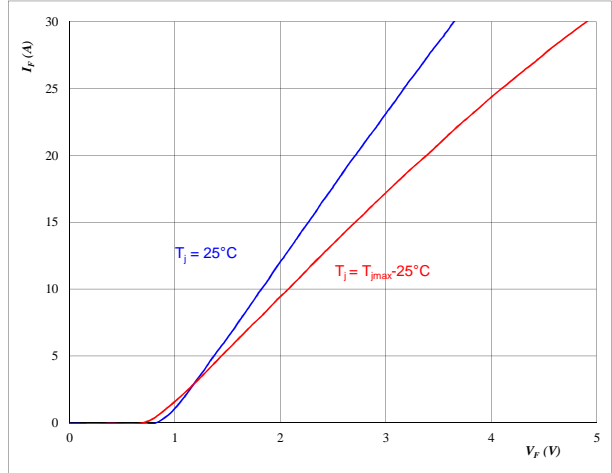
At

$t_p = 250 \mu s$   
 $T_j = 125 \text{ }^\circ C$   
 $U_{CC}$  from 7 V to 17 V in steps of 1 V

figure 3. PFC FWD

Typical diode forward current as a function of forward voltage

$I_F = f(V_F)$



At

$t_p = 250 \mu s$

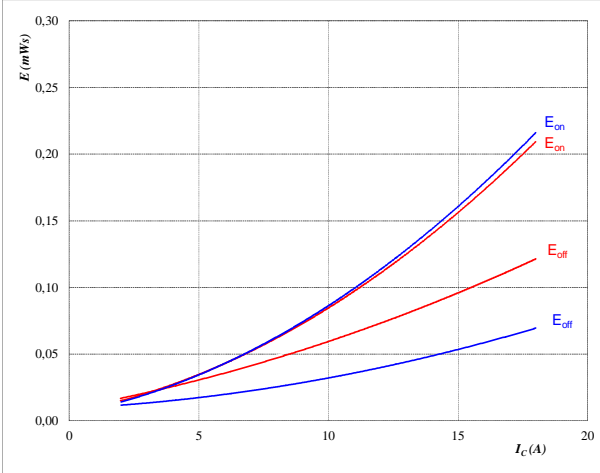


PFC

figure 4. PFC IGBT

Typical switching energy losses as a function of collector current

$E = f(I_c)$



With an inductive load at

$T_j = 25/125 \text{ } ^\circ\text{C}$

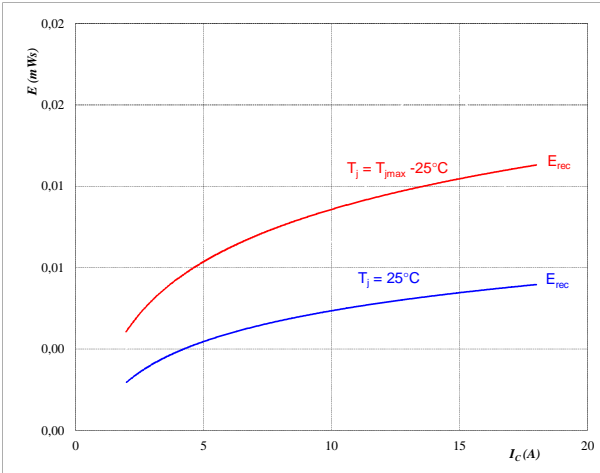
$V_{CE} = 400 \text{ V}$

$U_{CC} = 15 \text{ V}$

figure 5. PFC IGBT

Typical reverse recovery energy loss as a function of collector current

$E_{rec} = f(I_c)$



With an inductive load at

$T_j = 25/125 \text{ } ^\circ\text{C}$

$V_{CE} = 400 \text{ V}$

$U_{CC} = 15 \text{ V}$

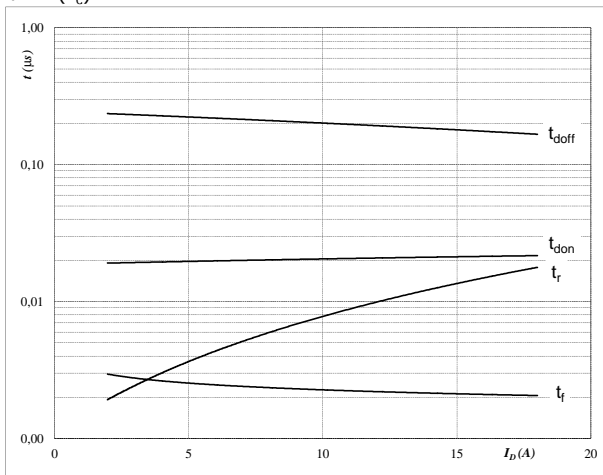


PFC

figure 6. PFC IGBT

Typical switching times as a function of collector current

$t = f(I_C)$



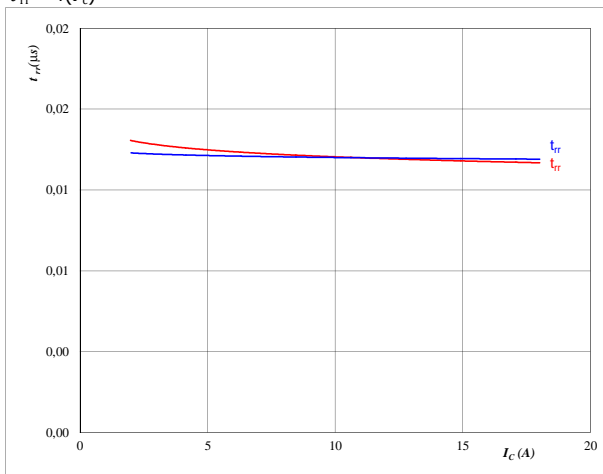
With an inductive load at

- $T_j = 125 \text{ } ^\circ\text{C}$
- $V_{CE} = 400 \text{ V}$
- $U_{CC} = 15 \text{ V}$

figure 7. PFC FWD

Typical reverse recovery time as a function of collector current

$t_{rr} = f(I_C)$



At

- $T_j = 25/125 \text{ } ^\circ\text{C}$
- $V_{CE} = 400 \text{ V}$
- $U_{CC} = 15 \text{ V}$



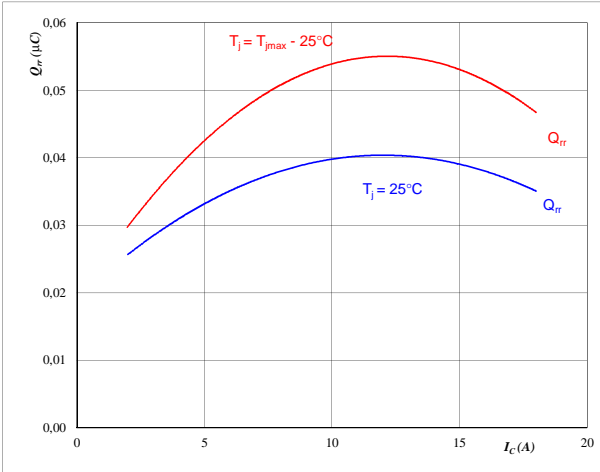


PFC

figure 8. PFC FWD

Typical reverse recovery charge as a function of collector current

$Q_{rr} = f(I_c)$



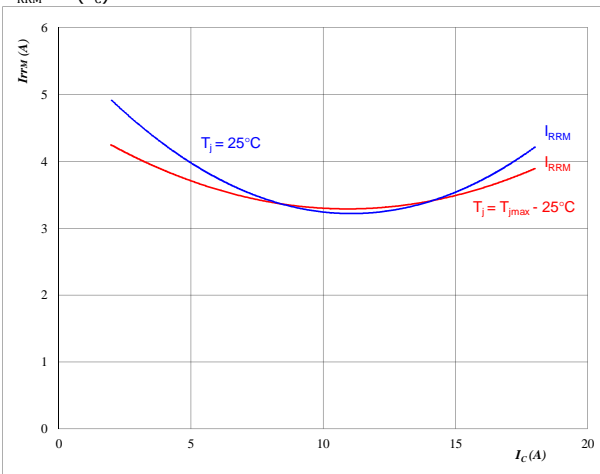
At

- $T_j = 25/125 \text{ } ^\circ\text{C}$
- $V_{CE} = 400 \text{ V}$
- $U_{CC} = 15 \text{ V}$

figure 9. PFC FWD

Typical reverse recovery current as a function of collector current

$I_{RRM} = f(I_c)$



At

- $T_j = 25/125 \text{ } ^\circ\text{C}$
- $V_{CE} = 400 \text{ V}$
- $U_{CC} = 15 \text{ V}$

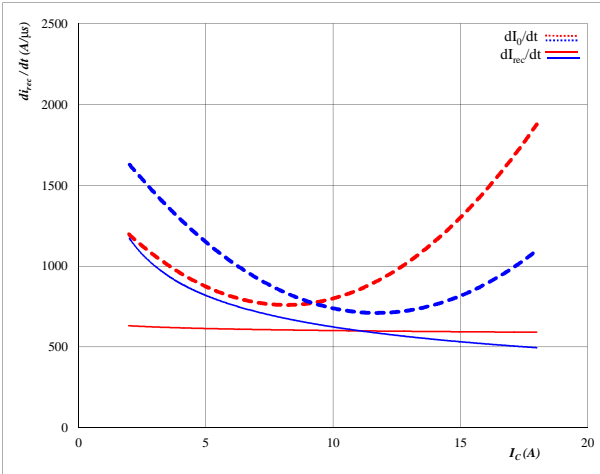


PFC

**figure 10. PFC FWD**

**Typical rate of fall of forward and reverse recovery current as a function of collector current**

$dI_0/dt, dI_{rec}/dt = f(I_c)$

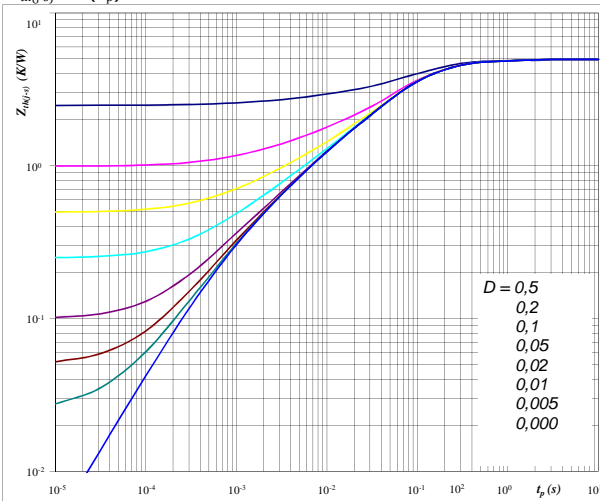


**At**  
 $T_j = 25/125 \text{ } ^\circ\text{C}$   
 $V_{CE} = 400 \text{ V}$   
 $U_{CC} = 15 \text{ V}$

**figure 11. PFC IGBT**

**IGBT transient thermal impedance as a function of pulse width**

$Z_{th(j-s)} = f(t_p)$



**At**  
 $D = t_p / T$   
 $R_{th(j-s)} = 4,96 \text{ K/W}$

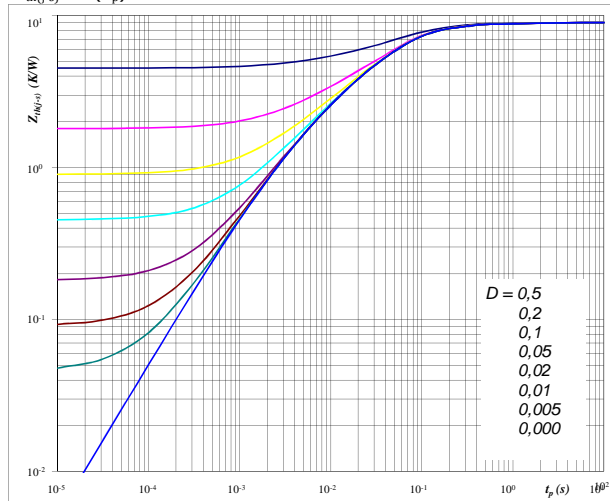
IGBT thermal model values

R (K/W)	Tau (s)
4,18E-01	7,75E-01
2,55E+00	1,04E-01
1,29E+00	3,31E-02
5,60E-01	3,97E-03
1,42E-01	5,99E-04

**figure 12. PFC FWD**

**FWD transient thermal impedance as a function of pulse width**

$Z_{th(j-s)} = f(t_p)$



**At**  
 $D = t_p / T$   
 $R_{th(j-s)} = 9,02 \text{ K/W}$

FWD thermal model values

R (K/W)	Tau (s)
2,70E-01	2,21E+00
9,02E-01	2,29E-01
5,68E+00	5,28E-02
1,76E+00	9,35E-03
4,06E-01	1,91E-03

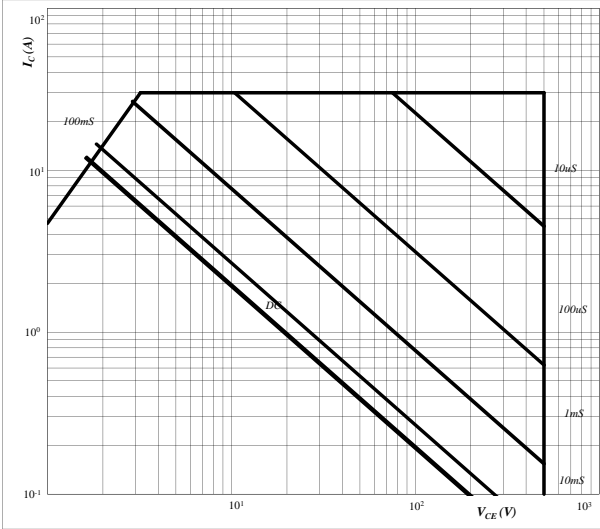


PFC

figure 17. PFC IGBT

Safe operating area as a function of collector-emitter voltage

$I_C = f(V_{CE})$



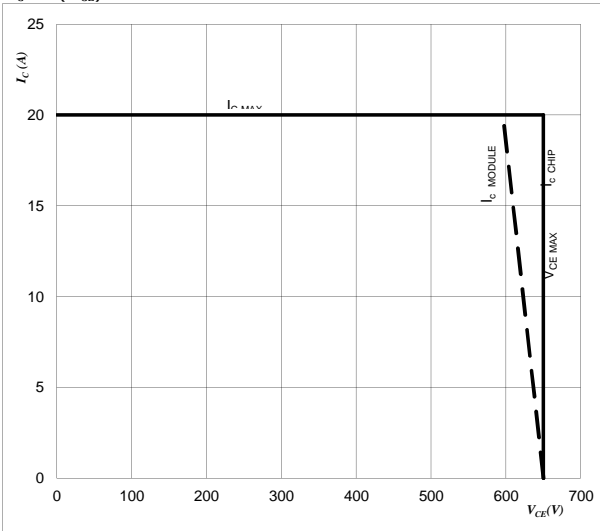
At

- $D =$  single pulse
- $T_s =$  80 °C
- $U_{CC} =$  15 V
- $T_j = T_{jmax}$

figure 18. PFC IGBT

Reverse bias safe operating area

$I_C = f(V_{CE})$



At

- $T_j = T_{jmax} - 25$  °C

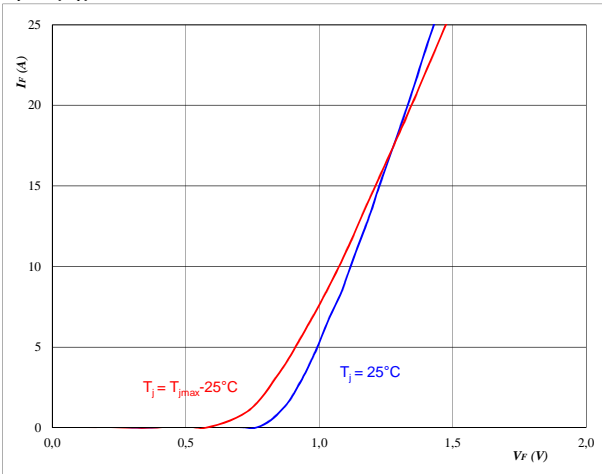


### Input Rectifier Diode

figure 1. Rectifier Diode

Typical diode forward current as a function of forward voltage

$I_F = f(V_F)$

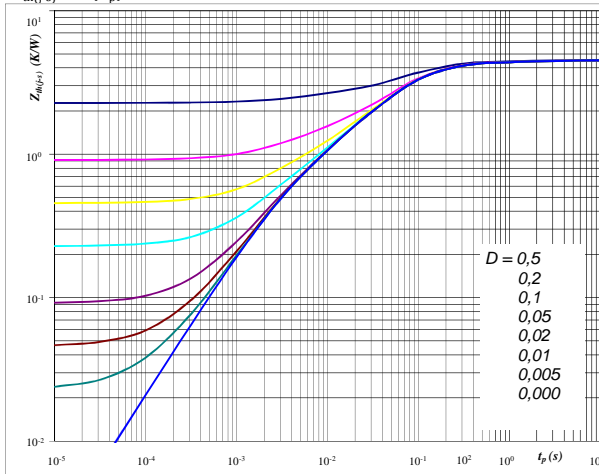


At  $t_p = 250 \mu s$

figure 2. Rectifier Diode

Diode transient thermal impedance as a function of pulse width

$Z_{th(j-s)} = f(t_p)$



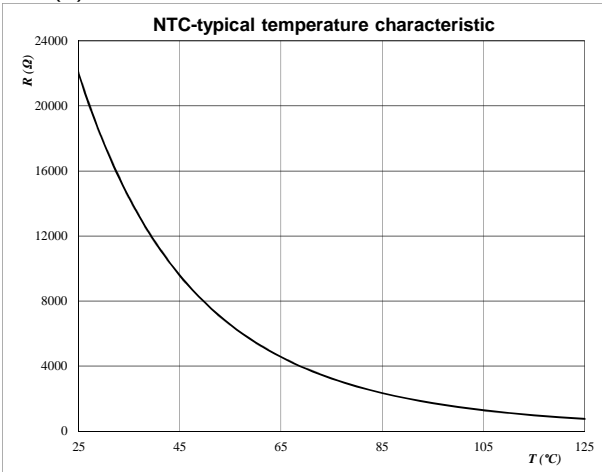
At  $D = t_p / T$   
 $R_{th(j-s)} = 4,56 \text{ K/W}$

### Thermistor

figure 1. Thermistor

Typical NTC characteristic as a function of temperature

$R = f(T)$





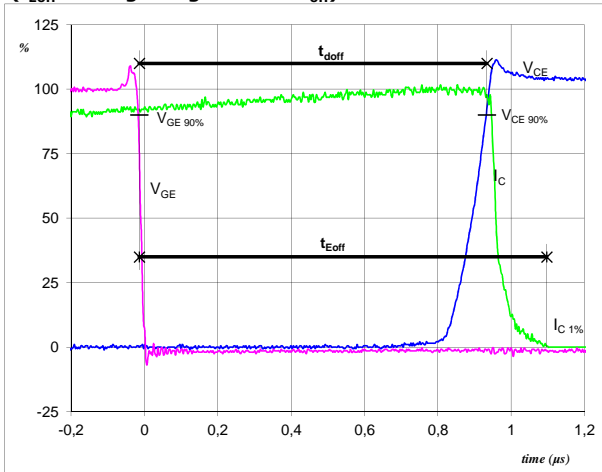
## Switching Definitions Output Inverter

General conditions

$T_j = 125\text{ °C}$

**figure 1. Output inverter IGBT**

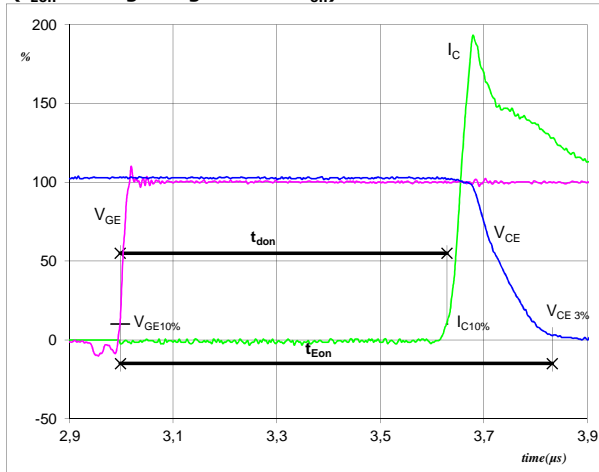
**Turn-off Switching Waveforms & definition of  $t_{doff}$ ,  $t_{Eoff}$**   
 ( $t_{Eoff}$  = integrating time for  $E_{off}$ )



$U_{IN} (0\%) =$	0	V
$U_{IN} (100\%) =$	5	V
$V_C (100\%) =$	400	V
$I_C (100\%) =$	6	A
$t_{doff} =$	0,95	$\mu\text{s}$
$t_{Eoff} =$	1,11	$\mu\text{s}$

**figure 2. Output inverter IGBT**

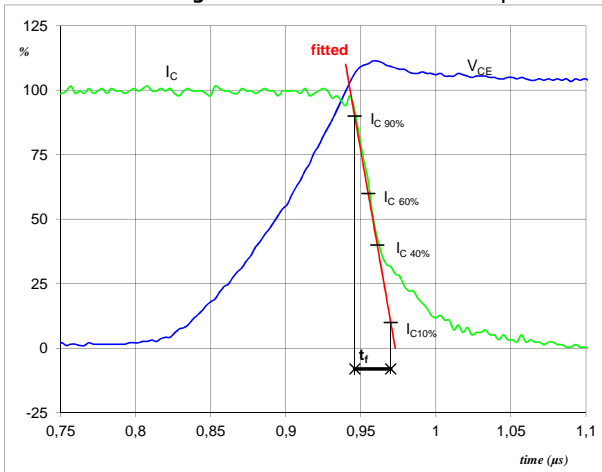
**Turn-on Switching Waveforms & definition of  $t_{don}$ ,  $t_{Eon}$**   
 ( $t_{Eon}$  = integrating time for  $E_{on}$ )



$U_{IN} (0\%) =$	0	V
$U_{IN} (100\%) =$	5	V
$V_C (100\%) =$	400	V
$I_C (100\%) =$	6	A
$t_{don} =$	0,63	$\mu\text{s}$
$t_{Eon} =$	0,83	$\mu\text{s}$

**figure 3. Output inverter IGBT**

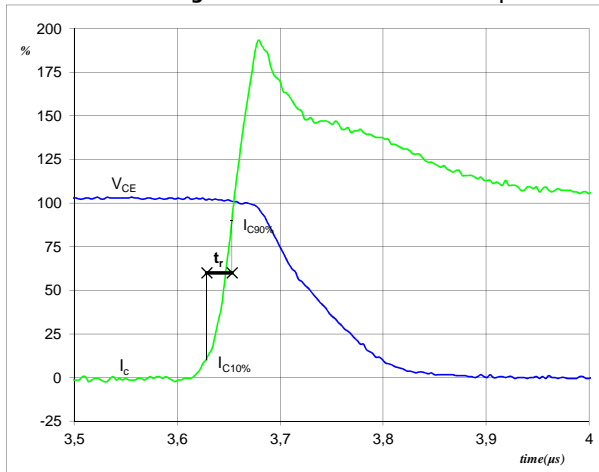
**Turn-off Switching Waveforms & definition of  $t_f$**



$V_C (100\%) =$	400	V
$I_C (100\%) =$	6	A
$t_f =$	0,02	$\mu\text{s}$

**figure 4. Output inverter IGBT**

**Turn-on Switching Waveforms & definition of  $t_r$**

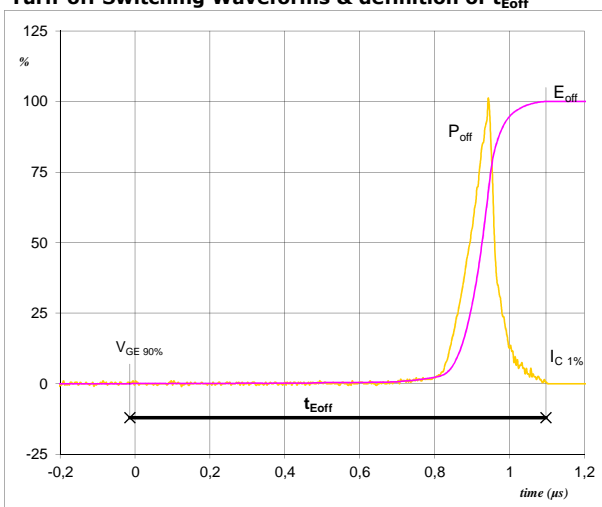


$V_C (100\%) =$	400	V
$I_C (100\%) =$	6	A
$t_r =$	0,03	$\mu\text{s}$



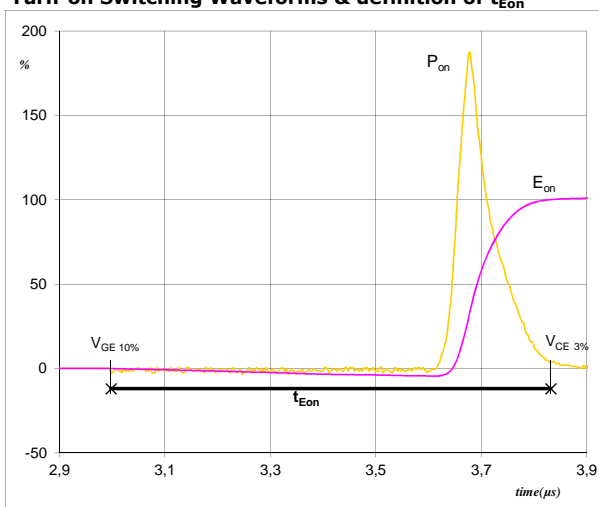
## Switching Definitions Output Inverter

**figure 5. Output inverter IGBT**  
Turn-off Switching Waveforms & definition of  $t_{Eoff}$



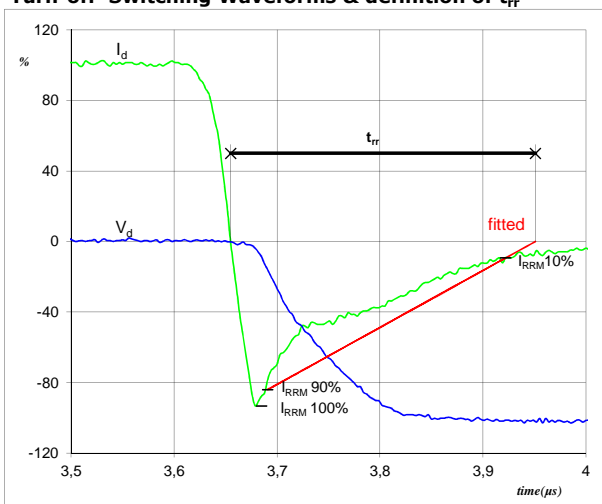
$P_{off}(100\%) = 2,39 \text{ kW}$   
 $E_{off}(100\%) = 0,20 \text{ mJ}$   
 $t_{Eoff} = 1,11 \text{ μs}$

**figure 6. Output inverter IGBT**  
Turn-on Switching Waveforms & definition of  $t_{Eon}$



$P_{on}(100\%) = 2,39 \text{ kW}$   
 $E_{on}(100\%) = 0,32 \text{ mJ}$   
 $t_{Eon} = 0,83 \text{ μs}$

**figure 7. Output inverter FWD**  
Turn-off Switching Waveforms & definition of  $t_{rr}$

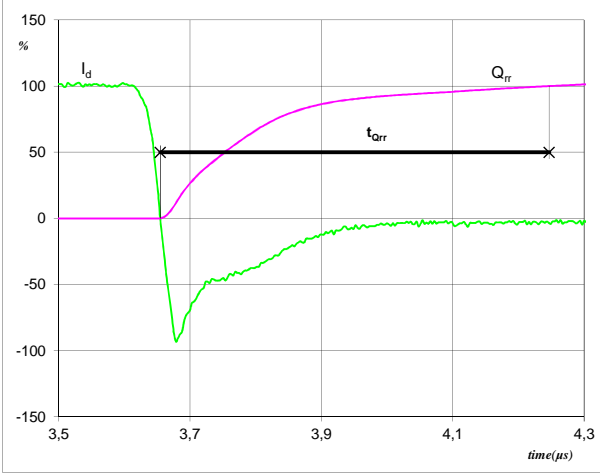


$V_d(100\%) = 400 \text{ V}$   
 $I_d(100\%) = 6 \text{ A}$   
 $I_{RRM}(100\%) = -6 \text{ A}$   
 $t_{rr} = 0,28 \text{ μs}$



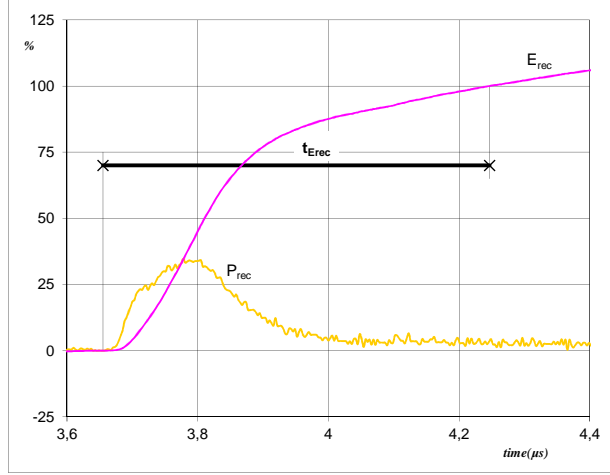
### Switching Definitions Output Inverter

**figure 8. Output inverter FWD**  
**Turn-on Switching Waveforms & definition of  $t_{Qrr}$**   
( $t_{Qrr}$  = integrating time for  $Q_{rr}$ )



$I_d$ (100%) =	6	A
$Q_{rr}$ (100%) =	0,67	$\mu\text{C}$
$t_{Qrr}$ =	0,59	$\mu\text{s}$

**figure 9. Output inverter FWD**  
**Turn-on Switching Waveforms & definition of  $t_{Erec}$**   
( $t_{Erec}$  = integrating time for  $E_{rec}$ )



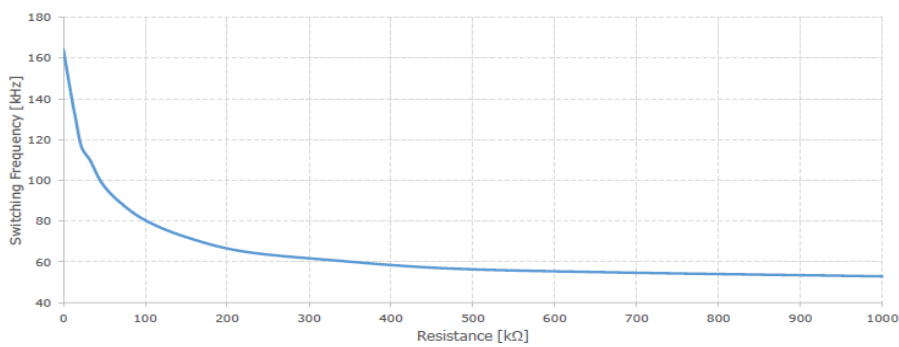
$P_{rec}$ (100%) =	2,39	kW
$E_{rec}$ (100%) =	0,16	mJ
$t_{Erec}$ =	0,59	$\mu\text{s}$

### Application data

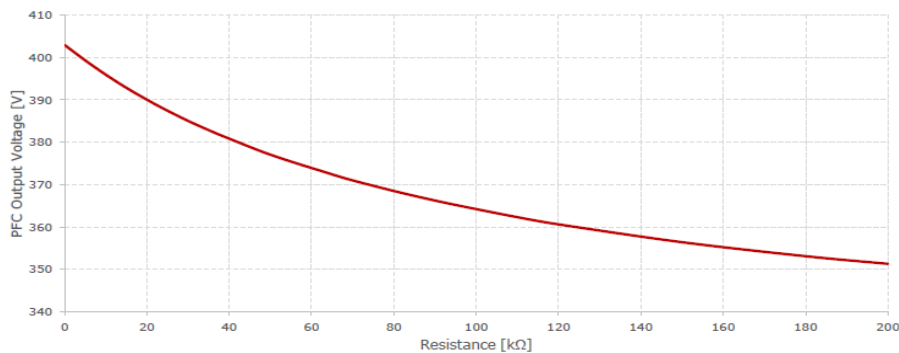
Static logic function table

$V_{CC}$	$V_{BS}$	RCIN	ITRIP	ENABLE	FAULT	LO1,2,3	HO1,2,3
$<V_{CCUV-}$	X	X	X	X	0	0	0
15V	$<V_{BSUV-}$	X	0	3.3V	High imp	/LIN1,2,3	0
15V	15V	$<3.2V_{\downarrow}$	0	3.3V	0	0	0
15V	15V	X	$>V_{IT,TH+}$	3.3V	0	0	0
15V	15V	$>V_{RCIN,TH}$	0	3.3V	High imp	/LIN1,2,3	/HIN1,2,3
15V	15V	$>V_{RCIN,TH}$	0	0	High imp	0	0

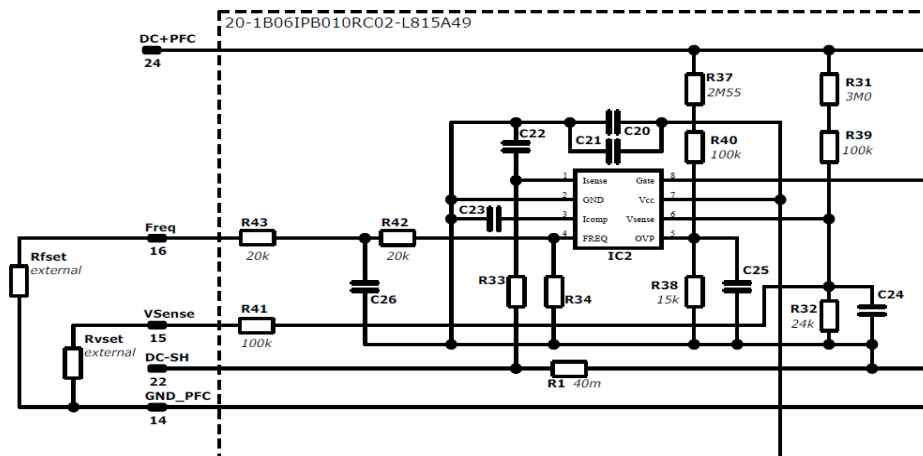
References for externally settable parameters



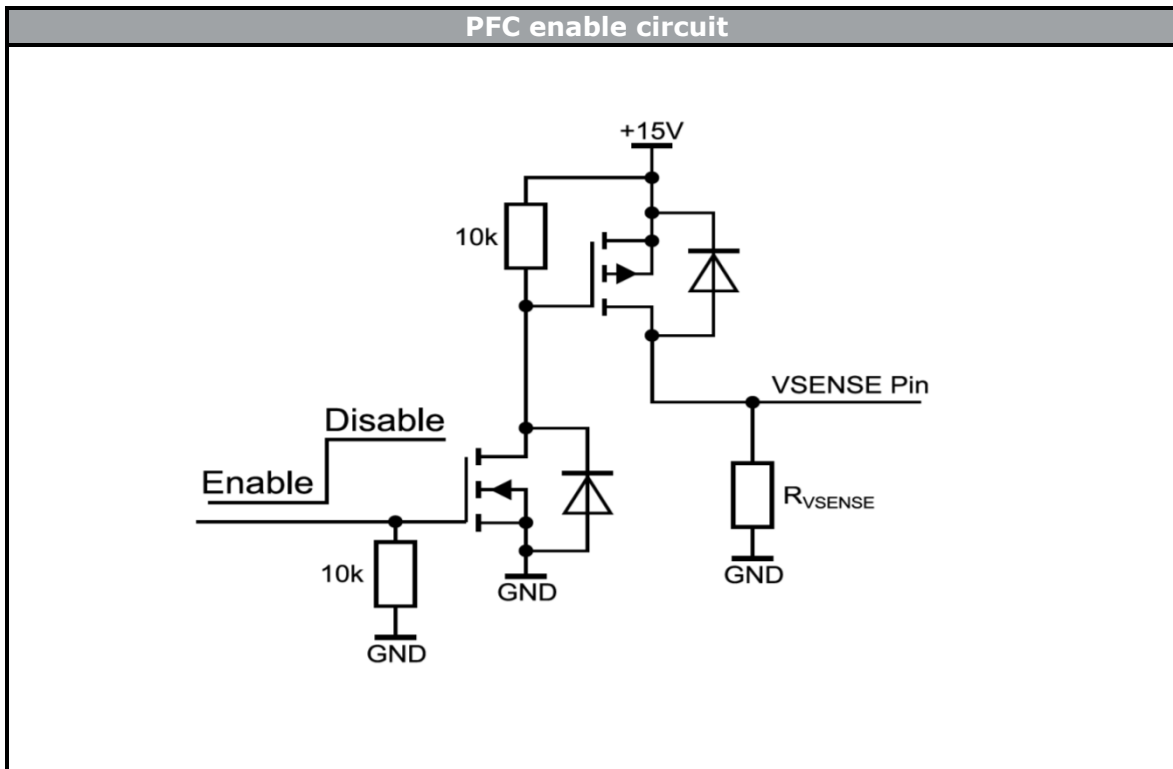
$R_{fset}$ [kΩ]	Switching Frequency [kHz]
0	164
10	141
15	130
22	117
33	110
47	99
68	90
100	80
150	72
220	65
330	61
470	57
680	55
1000	53



$R_{Vset}$ [kΩ]	Output Voltage [V]
0	403
5,1	399
10	396
15	393
20	390
24	388
30	385
36	382
39	381
47	378
51	377
56	375
62	373
68	372
75	370
82	368
91	366
100	364
110	362
120	361
150	356
180	353
200	351







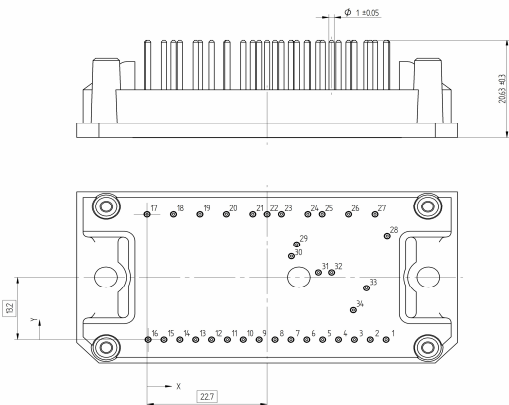
**Pin Descriptions**

Pin #	Pin Name	Pin Description
1	Therm1	Temperature sensor connector 1
2	COM	Low-side gate driver reference
3	ITRIP	Analog input for over-current shot down, activates FAULT
4	EN	Enable I/O functionality
5	-Fault	Fault output, indicates over current or under voltage (negative logic, open-drain)
6	-LIN3	Signal input for low-side Ph3 phase
7	-LIN2	Signal input for low-side Ph2 phase
8	-LIN1	Signal input for low-side Ph1 phase
9	-HIN3	Signal input for high-side Ph3 phase
10	-HIN2	Signal input for high-side Ph2 phase
11	-HIN1	Signal input for high-side Ph1 phase
12	V <sub>CC</sub>	Driver circuit supply voltage
13	GND_INV	Inverter ground
14	GND_PFC	PFC ground
15	VSENSE	PFC Bulk voltage sense
16	FREQ	PFC Switching frequency adjust
17	ACIn1	Rectifier input
18	ACIn2	Rectifier input
19	DC+Rect	Rectifier output DC +
20	PFC	PFC coil connector
21	DC-Rect	Rectifier output DC -
22	DC-SH	Current Sense Input for PFC Controller
23	DC-PFC	PFC capacitor GND (internally connected to GND_PFC)
24	DC+PFC	PFC capacitor + (output of the PFC stage)
25	DC+INV	Inverter input DC +
26	Ph3	Output for Ph3 phase
27	Ph2	Output for Ph2 phase
28	Ph1	Output for Ph1 phase
29	DC-3	Inverter input DC - for Ph3
30	DC-3SH+	Inverter Sense Resistor for Ph3 - High Side
31	DC-2SH+	Inverter Sense Resistor for Ph2 - High Side
32	DC-2	Inverter input DC - for Ph2
33	DC-1	Inverter input DC - for Ph1
34	DC-1SH+	Inverter Sense Resistor for Ph2 - High Side

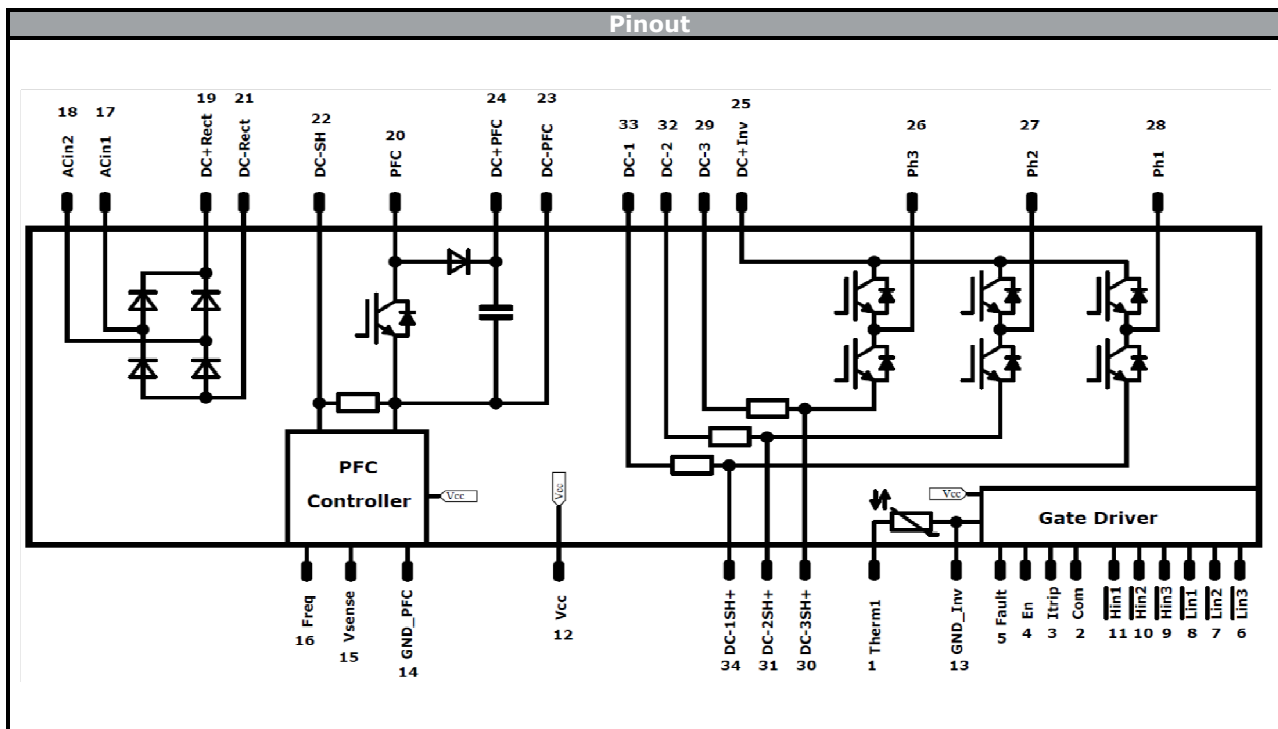


Ordering Code & Marking						
<b>Version</b>			<b>Ordering Code</b>			
without thermal paste 17 mm housing with solder pins			20-1B06IPB010RC02-L815A49			
with thermal paste 17 mm housing with solder pins			20-1B06IPB010RC02-L815A49-/3/			
			<b>Name</b>	<b>Date code</b>	<b>UL &amp; VIN</b>	<b>Lot</b>
<b>Text</b>			NN-NNNNNNNNNNNNNN-TTTTTTVV	WWYY	UL VIN	LLLLL SSSS
<b>Datamatrix</b>			<b>Type&amp;Ver</b>	<b>Lot number</b>	<b>Serial</b>	<b>Date code</b>
			TTTTTTTVV	LLLLL	SSSS	WWYY

Outline							
Pin table [mm]				Pin table [mm]			
Pin	X	Y	Function	Pin	X	Y	Function
1	45,2	0	NTC	19	10	26,4	DC+Rect
2	42,2	0	COM	20	15	26,4	PFC
3	39,2	0	ITRIP	21	20	26,4	DC-Rect
4	36,2	0	EN	22	22,7	26,4	DC-SH
5	33,2	0	FAULT	23	25,4	26,4	DC-PFC
6	30,2	0	LIN3	24	30,4	26,4	DC+PFC
7	27,2	0	LIN2	25	33,1	26,4	DC+Inv
8	24,2	0	LIN1	26	38,1	26,4	Ph3
9	21,2	0	HIN3	27	43,1	26,4	Ph2
10	18,2	0	HIN2	28	45,4	21,9	Ph1
11	15,2	0	HIN1	29	28,3	20,1	DC-3
12	12,2	0	VCC	30	27,3	17,6	DC-3SH
13	9,2	0	GND_INV	31	32,4	14,2	DC-2SH
14	6,2	0	GND_PFC	32	34,9	14,2	DC-2
15	3,2	0	VSEN	33	41,5	10,9	DC-1
16	0,2	0	FREQ	34	39	6,3	DC-1SH
17	0	26,4	ACIn1				
18	5	26,4	ACIn2				



Tolerance of pinposition: ±0.5mm at the end of pins  
Dimension of coordinate axis is only offset without tolerance



Identification					
ID	Component	Voltage	Current	Function	Comment
T1-T6	IGBT	600 V	10 A	Inverter Switch	
T27	IGBT	650 V	30 A	PFC Switch	
D27	FWD	650 V	8 A	PFC Diode	
D47	FWD	650 V	6 A	PFC Inverse Diode	
R4	Resistor			PFC Shunt	
D31-D34	Rectifier	1600 V	7 A	Rectifier Diode	
R1-R3	Resistor			DC Link Shunt	
C1	Capacitor	500 V		Capacitor (DC)	
Rt	Thermistor			Thermistor	



Packaging instruction			
Standard packaging quantity (SPQ)	<b>100</b>	>SPQ	Standard
		<SPQ	Sample

Handling instruction
Handling instructions for <i>flow</i> 1B packages see vincotech.com website.

Package data
Package data for <i>flow</i> 1B packages see vincotech.com website.

UL recognition and file number
This device is certified according to UL 1557 standard, UL file number E192116. For more information see vincotech.com website.



Document No.:	Date:	Modification:	Pages
20-1B06IPB010RC02-L815A49-D5-14	18 Sept. 2020	Update condition of OVP parameters Add simplified schematic to show Rvset, Rfset resistor Correct Pin description table	7 24 25

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